

N-channel Enhancement Mode Power MOSFET

Features

- Very Low On-resistance $R_{DS(ON)}$
- Low C_{rss}
- 100% avalanche tested
- Improved dv/dt capability

Applications

- PWM Application
- Motor drivers
- DC/DC Converter

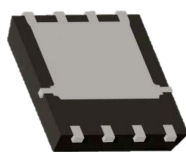
Product Summary

Parameters	Value	Unit
V_{DSS}	60	V
$V_{GS(th_Typ)}$	1.5	V
$I_D(@V_{GS}=10V)$	270	A
$R_{DS(ON_Typ)}(@V_{GS}=10V)$	1.2	$m\Omega$
$R_{DS(ON_Typ)}(@V_{GS}=4.5V)$	1.8	$m\Omega$

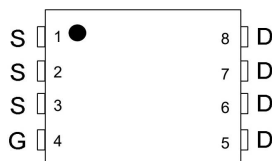
Top View



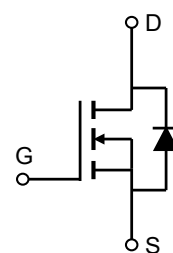
Bottom View



PDFN5x6-8L



Marking



Schematic Diagram

Ordering Information

Device	Marking	Package	Packing	Reel Size	Tape Width	Reel (pcs)
ZK60G270G	60G270	PDFN5x6	Reel	N/A	N/A	5000

MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^{\circ}C$	I_D	270	A
	$T_C = 100^{\circ}C$		130	
Pulsed Drain Current		I_{DM}	1200	A
Single Pulsed Avalanche Energy		E_{AS}	990	mJ
Power Dissipation		P_D	375	W
Thermal Resistance from Junction to Ambient		$R_{\theta JA}$	60	$^{\circ}C/W$
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS

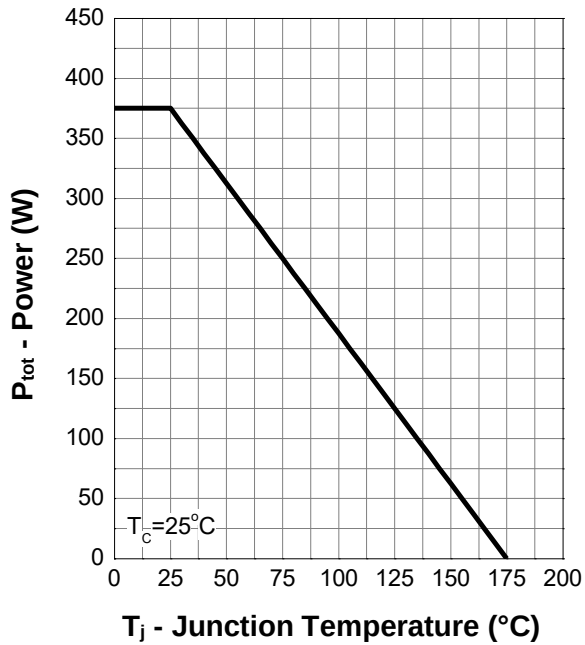
$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} =±20V			±100	nA
On characteristics ④						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.5	2.8	3.2	V
Static drain-source on-sate resistance	R _{DS(on)}	V _{GS} =10V, I _D =15A		1.2	1.6	mΩ
		V _{GS} =4.5V, I _D =20A		1.8	2.2	mΩ
Dynamic characteristics ④ ⑤						
Input capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V f =1MHz		6900		pF
Output capacitance	C _{oss}			2600		
Reverse transfer capacitance	C _{rss}			120		
Gate resistance	R _g	f =1MHz		2		Ω
Switching characteristics ④ ⑤						
Total gate charge	Q _g	V _{GS} =0 to 10V V _{DS} =30V, I _D =30A		155		nC
Gate-source charge	Q _{gs}			25		
Gate-drain charge	Q _{gd}			35		
Turn-on delay time	t _{d(on)}	V _{DS} =30V, I _D =30A V _{GS} =10V, R _{GEN} =3.9Ω		16		ns
Turn-on rise time	t _r			56		
Turn-off delay time	t _{d(off)}			149		
Turn-off fall time	t _f			96		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage	V _{SD} ④	V _{GS} =0V, I _{SD} =30A			1.3	V
Continuous drain-source diode forward current	I _S ①	T _C =25℃			140	A
Reverse recovery time	trr	di/dt = 100A/μs, I _F = 30A		85		ns
Reverse recovery charge	Qrr			120		nC

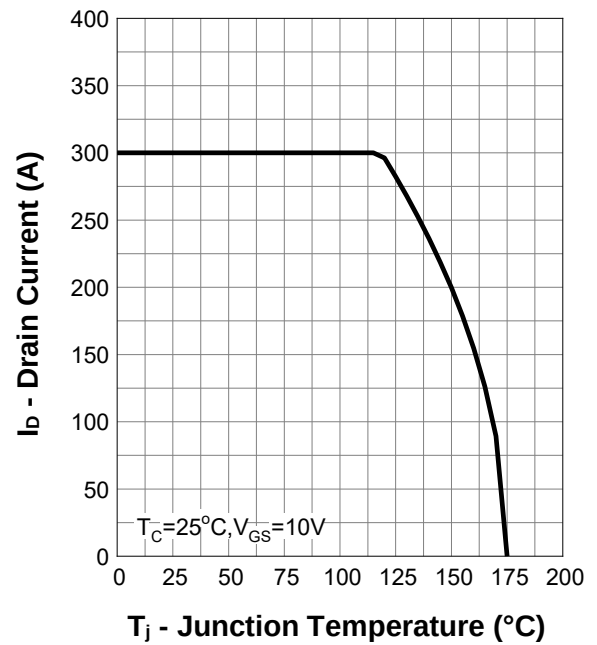
Notes:

1. Guaranteed by design, not subject to production testing
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycles $\leq 2\%$

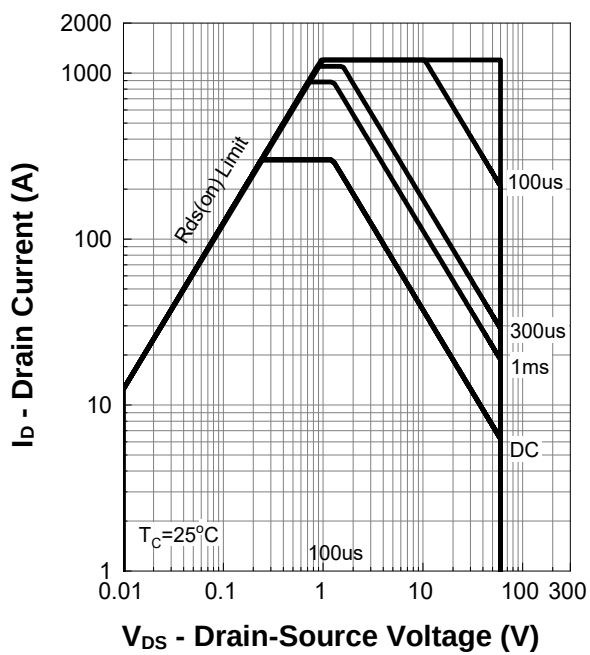
Power Capability



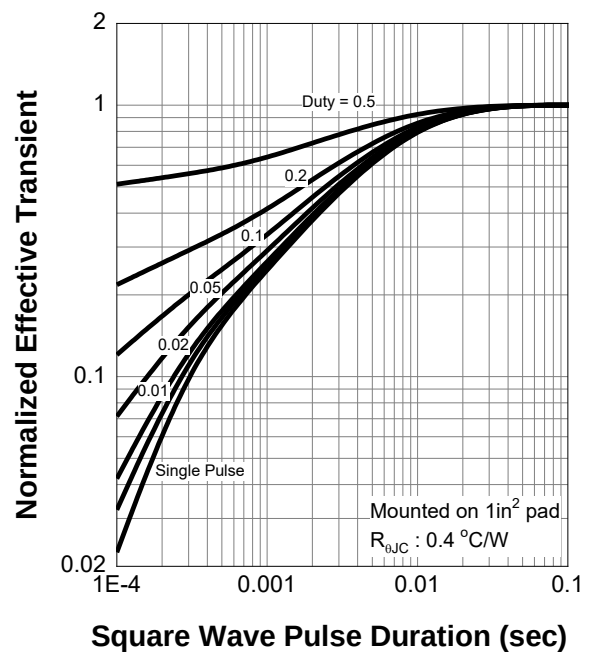
Current Capability



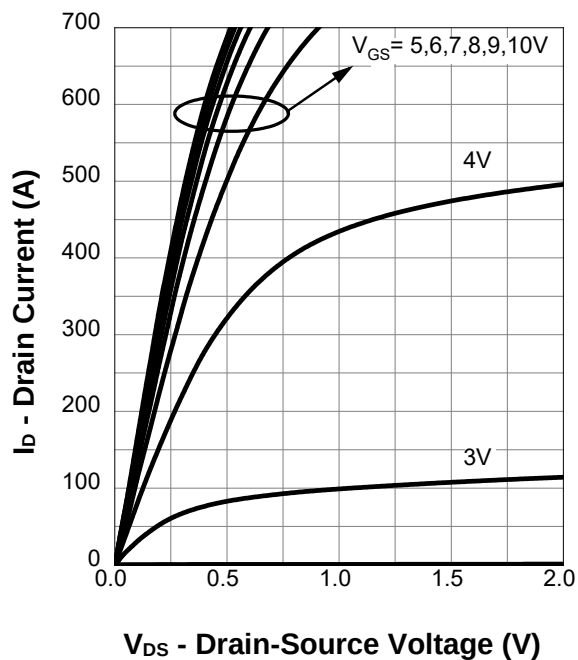
Safe Operation Area



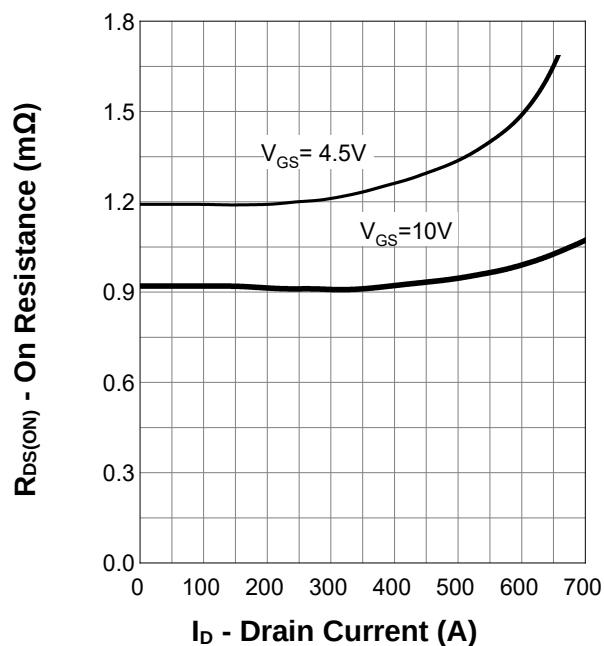
Transient Thermal Impedance



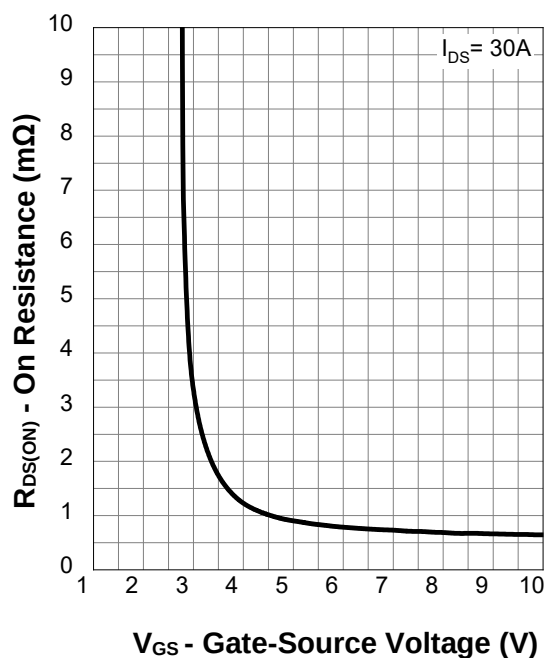
Output Characteristics



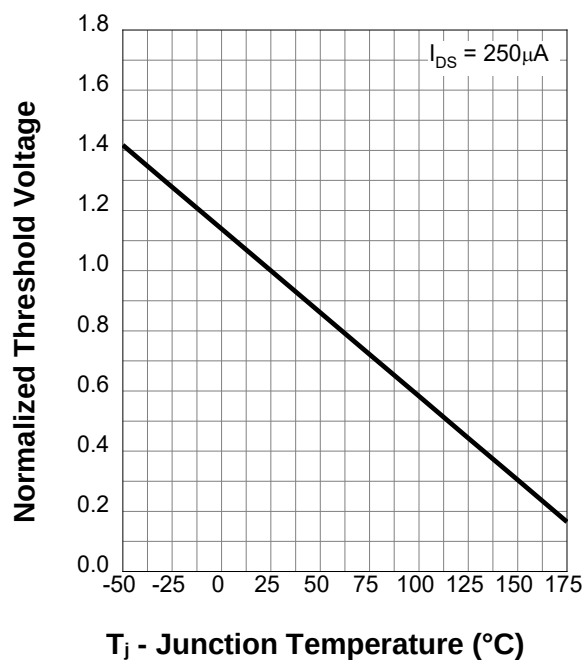
On Resistance



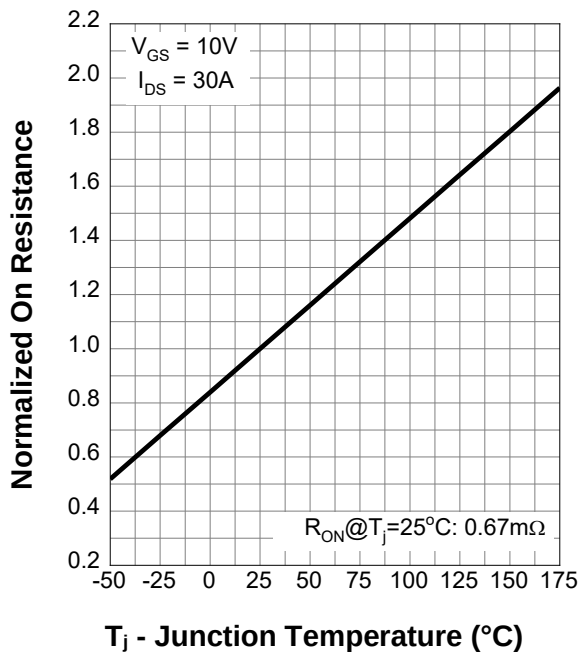
Transfer Characteristics



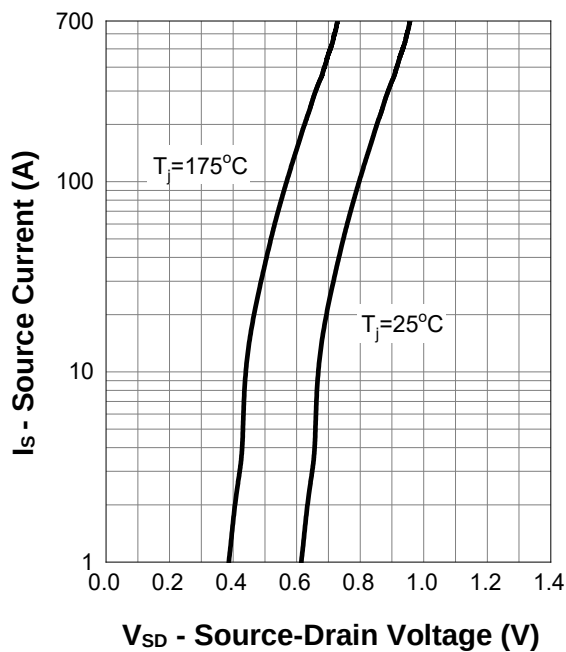
Normalized Threshold Voltage



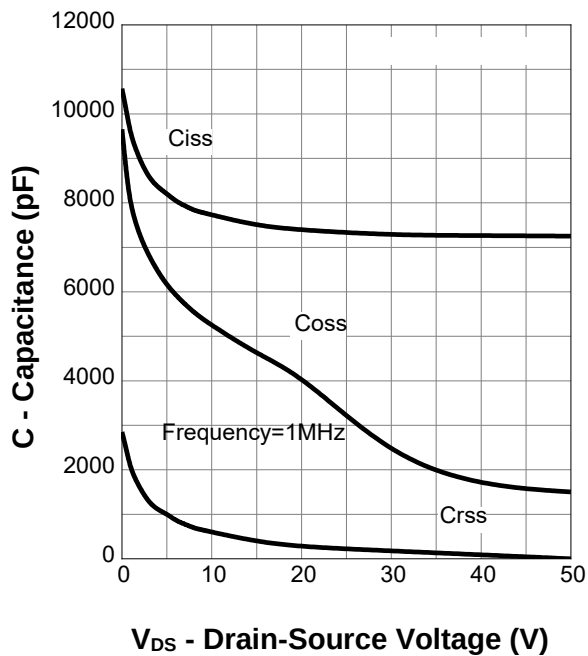
Normalized On Resistance



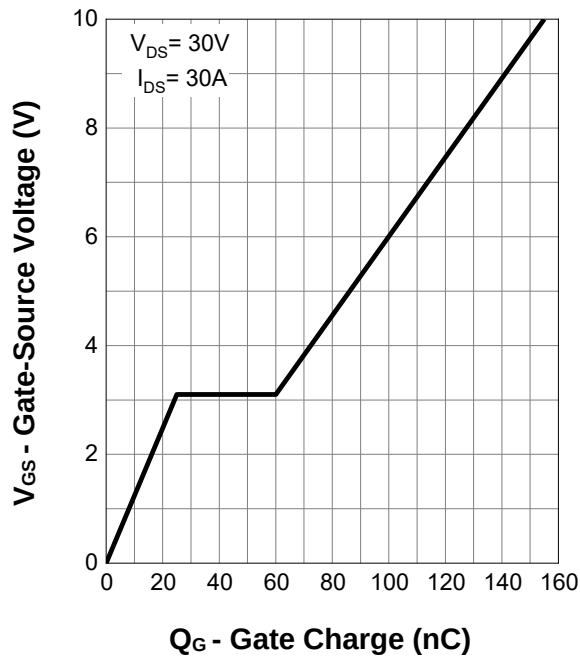
Diode Forward Current

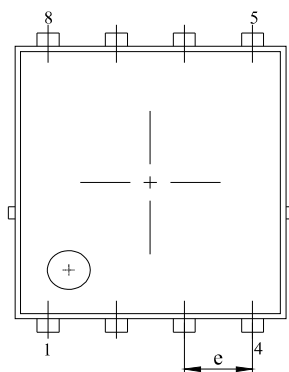


Capacitance

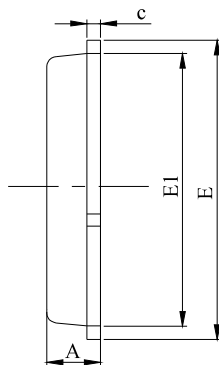


Gate Charge

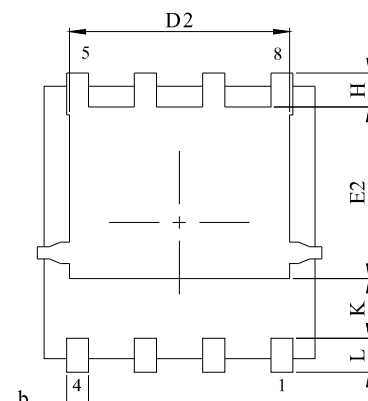




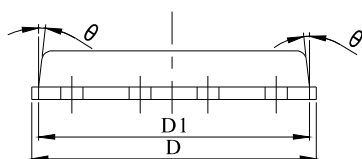
Top View



Side View



Bottom View



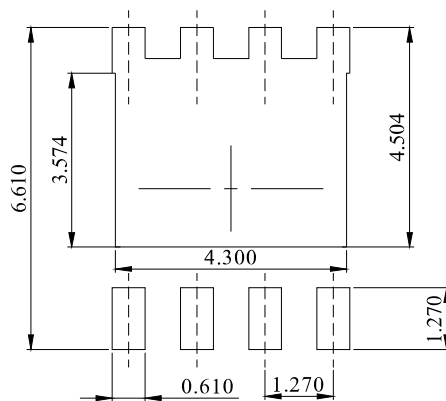
Front View

NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions D1 and E1 do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
c	0.20	0.25	0.30
D	5.00	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.42	3.53	3.63
e	1.27BSC		
H	0.60	0.70	0.80
L	0.50	0.70	0.80
K	1.23 REF		
θ	-	-	10°

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS